

**Amendments to the Specification:**

Please replace the title as follows:

ELECTROLUMINESCENT DEVICE WITH BARRIER LAYER STRUCTURE, METHOD  
FOR MANUFACTURING THE SAME, AND ELECTRONIC APPARATUS

Please replace paragraph [0042] with the following rewritten paragraph:

[0042] The EL device 10 can include the barrier layer 52, which is composed of at least one ~~sublayer~~sublayer 53. The barrier layer 52 is transparent (for example, the barrier layer 52 has an optical transmittance of at least 80%). The barrier layer 52 is formed in contact with the second electrode 50. At least the surface of the barrier layer 52 facing the second electrode 50 is composed of an inorganic compound (for example, a silicon compound such as silicon oxide, silicon nitride, or silicon nitride oxide). The barrier layer 52 may include at least one sublayer composed of a silicon compound. The barrier layer 52 may include a sublayer composed of silicon oxide or silicon nitride, the sublayer contacting with the second electrode 50. The barrier layer 52 extends over the insulating layer 32. The barrier layer 52 has a thickness ranging from 10 nm to 300 nm, for example about 100 nm.